

remarks.

## **Amendment**

### **FOR THE SPECIFICATION**

[0028] In a preferred embodiment of the present invention, the following steps shown in FIG. 1B' and FIG. 1B'' can be performed between FIG. 1B and FIG. 1C. First, a lining oxide layer 107(not shown) is formed on the surface of the gate structure 105 and the substrate 100, as shown in FIG. 1B'. Then the lining oxide layer 107 is etched back so that only the sidewall of the gate structure 105 has the remaining lining oxide layer 107a thereon, as shown in FIG. 1B''. Then, the step shown in FIG. 1C is performed to form the metal silicide layer 108. Therefore, the metal silicide layer 108 would not be formed on the sidewall of the gate structure 105.